TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type ( $\pi$ -MOSVII)

# **TPCA8006-H**

Switching Regulator Applications
Motor Drive Applications
DC/DC Converter Applications

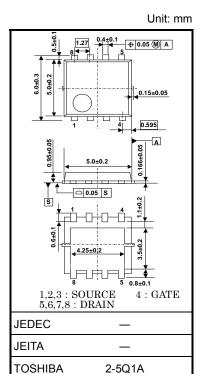
- Small footprint due to a small and thin package
- · High speed switching
- Low drain-source ON-resistance

: RDS (ON) = 41 mQ (typ.) (VG=10V, ID=9A)

- High forward transfer admittance:  $|Y_{fs}| = 15 \mathrm{S}$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \,\mu\text{A} \,(\text{max}) \,(V_{DS} = 100 \,\text{V})$
- Enhancement mode:  $V_{th} = 3.0 \text{ to } 5.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA)}$

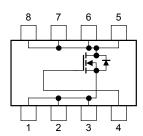
### Absolute Maximum Ratings (Ta = 25°C)

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	100	V	
Drain-gate voltage (R	$k_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	100	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	I <sub>D</sub>	18	А	
Diam current	Pulsed (Note 1)	$I_{DP}$	36		
Drain power dissipati	on (Tc=25°C)	PD	45	W	
Drain power dissipation $(t = 10 s)$ (Note 2a)		$P_{D}$	2.8	W	
Drain power dissipation (t = 10 s) (Note 2b)		P <sub>D</sub>	1.6	W	
Single-pulse avalanche energy (Note 3)		E <sub>AS</sub>	224	mJ	
Avalanche current		I <sub>AR</sub>	18	Α	
Repetitive avalanche energy (Note 2a) (Note 4)		E <sub>AR</sub>	4.5	mJ	
Channel temperature	Channel temperature		150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 0.069 g (typ.)

### **Circuit Configuration**



Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

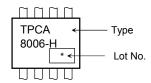
This transistor is an electrostatic-sensitive device. Handle with care.



### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc=25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

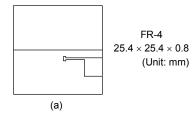
### Marking (Note 5)

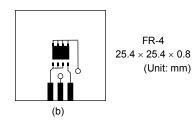


Note 1: The channel temperature should not exceed 150°C during use.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

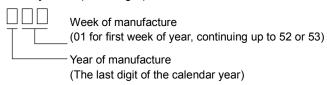




Note 3:  $V_{DD} = 50 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial), L = 0.8 mH,  $R_G = 25 \Omega$ ,  $I_{AR} = 18 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: \* Weekly code: (Three digits)

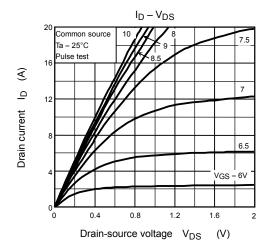


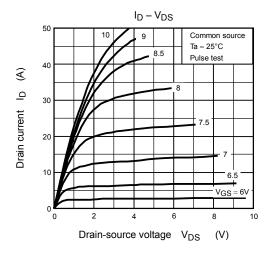
# Electrical Characteristics (Ta = 25°C)

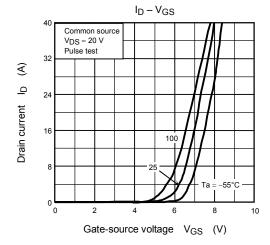
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$		_	100	μА
Drain-source bre	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	100	_	_	V
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	3.0	_	5.0	V
Drain-source ON	-resistance	R <sub>DS (ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9 A		41	67	mΩ
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_D = 9 \text{ A}$	7.5	15	_	S
Input capacitance	•	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		780	_	pF
Reverse transfer	capacitance	C <sub>rss</sub>			17	_	
Output capacitan	ce	Coss		_	390	_	
Switching time	Rise time	t <sub>r</sub>	Ves 10 V	_	3	_	
	Turn-on time	t <sub>on</sub>		_	13	_	
	Fall time	t <sub>f</sub>		_	2	_	ns
	Turn-off time	t <sub>off</sub>	$V_{DD} \simeq 50 \text{ V}$ Duty $\leq$ 1%, $t_W = 10 \mu\text{s}$	_	13	_	
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq 80 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 18 \text{ A}$	_	12	_	nC
Gate-source charge 1		Q <sub>gs1</sub>		_	5.6	_	
Gate-drain ("Miller") charge		Q <sub>gd</sub>		_	4.0	_	
Gate switch charge		$Q_{SW}$		_	6.9	_	

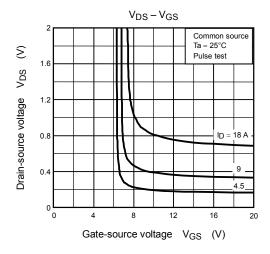
## Source-Drain Ratings and Characteristics (Ta = 25°C)

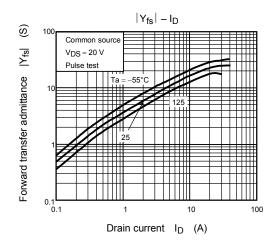
Characteri	stic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current	Pulse	I <sub>DRP</sub>	_	_	_	36	Α
Forward voltage (diode)		V <sub>DSF</sub>	$I_{DR} = 18 \text{ A}, V_{GS} = 0 \text{ V}$		_	-1.7	V

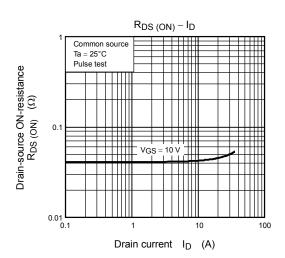




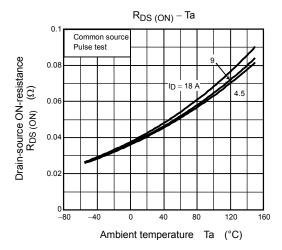


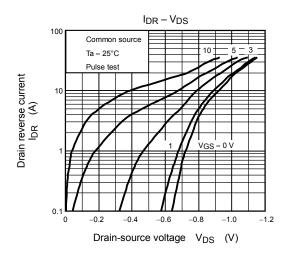


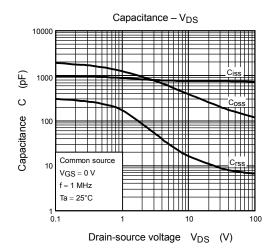


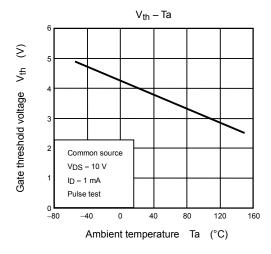


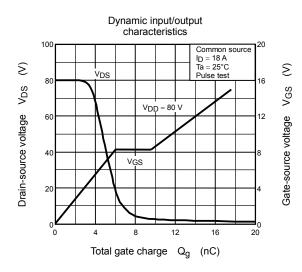
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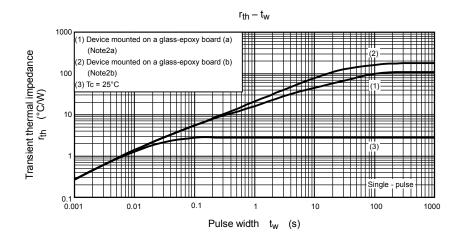


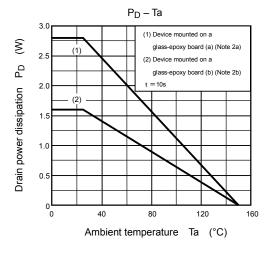


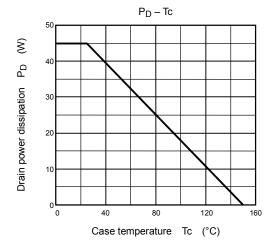


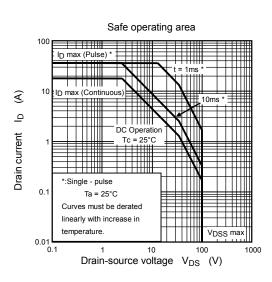


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Handbook" etc. 021023\_A

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